Jing Lu

List of Publications by Year
in descending order

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153

papers

7,672

citations

38660

50

h-index

60497

81

g-index

155

all docs

155

docs citations

155

times ranked

7390

citing authors

#	Article	IF	Citations
1	Quasiparticle energies and excitonic effects of the two-dimensional carbon allotrope graphdiyne: Theory and experiment. Physical Review B, 2011, 84, .	1.1	305
2	Tunable and sizable band gap in silicene by surface adsorption. Scientific Reports, 2012, 2, 853.	1.6	253
3	Many-body Effect, Carrier Mobility, and Device Performance of Hexagonal Arsenene and Antimonene. Chemistry of Materials, 2017, 29, 2191-2201.	3.2	244
4	Quantum spin Hall insulators and quantum valley Hall insulators of BiX/SbX (X=H, F, Cl and Br) monolayers with a record bulk band gap. NPG Asia Materials, 2014, 6, e147-e147.	3.8	242
5	Interfacial Properties of Monolayer and Bilayer MoS2 Contacts with Metals: Beyond the Energy Band Calculations. Scientific Reports, 2016, 6, 21786.	1.6	224
6	Oxygen Vacancy-Induced Nonradical Degradation of Organics: Critical Trigger of Oxygen (O₂) in the Feâ€“Co LDH/Peroxymonosulfate System. Environmental Science & Technology, 2021, 55, 15400-15411.	4.6	201
7	Monolayer Phosphoreneâ€“Metal Contacts. Chemistry of Materials, 2016, 28, 2100-2109.	3.2	199
8	High-performance sub-10 nm monolayer Bi₂O₂Se transistors. Nanoscale, 2019, 11, 532-540.	2.8	196
9	Selective Interaction of Large or Charge-Transfer Aromatic Molecules with Metallic Single-Wall Carbon Nanotubes:Â Critical Role of the Molecular Size and Orientation. Journal of the American Chemical Society, 2006, 128, 5114-5118.	6.6	168
10	Does p-type ohmic contact exist in WSe₂â€“metal interfaces?. Nanoscale, 2016, 8, 1179-1191.	2.8	166
11	Gd-doping effect on performance of HfO2 based resistive switching memory devices using implantation approach. Applied Physics Letters, 2011, 98, .	1.5	165
12	Tunable and sizable band gap of single-layer graphene sandwiched between hexagonal boron nitride. NPG Asia Materials, 2012, 4, e6-e6.	3.8	158
13	Ionic doping effect in ZrO2 resistive switching memory. Applied Physics Letters, 2010, 96, .	1.5	154
14	Simulations of Quantum Transport in Sub-5-nm Monolayer Phosphorene Transistors. Physical Review Applied, 2018, 10, .	1.5	144
15	Dendriteâ€Free Lithium Deposition via a Superfilling Mechanism for Highâ€Performance Liâ€Metal Batteries. Advanced Materials, 2019, 31, e1903248.	11.1	106
16	Magnetic Properties of Fully Bare and Half-Bare Boron Nitride Nanoribbons. Journal of Physical Chemistry C, 2009, 113, 2273-2276.	1.5	102
17	Structural, Electronic, and Optical Properties of Bulk Graphdiyne. Journal of Physical Chemistry C, 2013, 117, 13072-13079.	1.5	101
18	Many-Body Effect and Device Performance Limit of Monolayer InSe. ACS Applied Materials & Interfaces, 2018, 10, 23344-23352.	4.0	98

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19	Performance Upper Limit of subâ€10 nm Monolayer MoS₂ Transistors. Advanced Electronic Materials, 2016, 2, 1600191.	2.6	97
20	Schottky barrier heights in two-dimensional field-effect transistors: from theory to experiment. Reports on Progress in Physics, 2021, 84, 056501.	8.1	97
21	Schottky Barriers in Bilayer Phosphorene Transistors. ACS Applied Materials & Interfaces, 2017, 9, 12694-12705.	4.0	94
22	Does the Dirac Cone Exist in Silicene on Metal Substrates?. Scientific Reports, 2014, 4, 5476.	1.6	92
23	Nitrofullerene, a C₆₀-based Bifunctional Additive with Smoothing and Protecting Effects for Stable Lithium Metal Anode. Nano Letters, 2019, 19, 8780-8786.	4.5	83
24	XRD and Raman Studies on the Ordering/Disordering of Ba(Mg_{1/3}Ta_{2/3})O₃. Journal of the American Ceramic Society, 2009, 92, 1547-1551.	1.9	82
25	Valley pseudospin in monolayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi>Si</mml:mi><mml mathvariant="normal">N</mml:mi><mml:mn>4</mml:mn></mml:msub></mml:mrow></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi>Si</mml:mi><mml Physical Review B, 2021, 103, .	1.1	82
26	Monolayer tellureneâ€“metal contacts. Journal of Materials Chemistry C, 2018, 6, 6153-6163.	2.7	81
27	Epitaxial Singleâ€Layer MoS₂ on GaN with Enhanced Valley Helicity. Advanced Materials, 2018, 30, 1703888.	11.1	80
28	Sub-10Ânm two-dimensional transistors: Theory and experiment. Physics Reports, 2021, 938, 1-72.	10.3	80
29	Sub-5 nm Monolayer Arsenene and Antimonene Transistors. ACS Applied Materials & Interfaces, 2018, 10, 22363-22371.	4.0	77
30	Black phosphorus transistors with van der Waals-type electrical contacts. Nanoscale, 2017, 9, 14047-14057.	2.8	76
31	Electrical Contacts in Monolayer Arsenene Devices. ACS Applied Materials & Interfaces, 2017, 9, 29273-29284.	4.0	76
32	Ultra-narrow WS₂nanoribbons encapsulated in carbon nanotubes. Journal of Materials Chemistry, 2011, 21, 171-180.	6.7	74
33	Monolayer Bismuthene-Metal Contacts: A Theoretical Study. ACS Applied Materials & Interfaces, 2017, 9, 23128-23140.	4.0	73
34	Electric-Field-Induced Energy Gap in Few-Layer Graphene. Journal of Physical Chemistry C, 2011, 115, 9458-9464.	1.5	72
35	Three-layer phosphorene-metal interfaces. Nano Research, 2018, 11, 707-721.	5.8	72
36	Interfacial Properties of Monolayer MoSe₂â€“Metal Contacts. Journal of Physical Chemistry C, 2016, 120, 13063-13070.	1.5	70

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37	Can a Black Phosphorus Schottky Barrier Transistor Be Good Enough?. ACS Applied Materials & Interfaces, 2017, 9, 3959-3966.	4.0	70
38	Sub 10 nm Bilayer Bi₂O₂Se Transistors. Advanced Electronic Materials, 2019, 5, 1800720.	2.6	70
39	Designing sub-10-nm Metal-Oxide-Semiconductor Field-Effect Transistors via Ballistic Transport and Disparate Effective Mass: The Case of Two-Dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Bi</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math>. Physical Review Applied, 2020, 13, .	1.5	69
40	Why Semiconducting Singleâ€Walled Carbon Nanotubes are Separated from their Metallic Counterparts. Small, 2007, 3, 1566-1576.	5.2	68
41	Phase formations and magnetic properties of single crystal nickel ferrite (NiFe₂O₄) with different morphologies. CrystEngComm, 2015, 17, 1603-1608.	1.3	67
42	Excellent Device Performance of Subâ€5â€nm Monolayer Tellurene Transistors. Advanced Electronic Materials, 2019, 5, 1900226.	2.6	65
43	Firstâ€Principle Calculation and Assignment for Vibrational Spectra of <scp><scp>Ba</scp></scp>(<scp><scp>Mg</scp></scp>_{1/2}<scp><scp>W</scp></scp>_{1/2})<scp><scp>O</ Microwave Dielectric Ceramic. Journal of the American Ceramic Society, 2013, 96, 2898-2905.	1.9	63
44	A New Polyanion Na₃Fe₂(PO₄)P₂O₇ Cathode with High Electrochemical Performance for Sodium-Ion Batteries. ACS Energy Letters, 2020, 5, 3788-3796.	8.8	62
45	Allâ€Metallic Vertical Transistors Based on Stacked Dirac Materials. Advanced Functional Materials, 2015, 25, 68-77.	7.8	59
46	Sub-5 nm Monolayer MoS₂ Transistors toward Low-Power Devices. ACS Applied Electronic Materials, 2021, 3, 1560-1571.	2.0	56
47	Tunable band gap in few-layer graphene by surface adsorption. Scientific Reports, 2013, 3, .	1.6	55
48	Ohmic contacts between monolayer WSe2 and two-dimensional titanium carbides. Carbon, 2018, 135, 125-133.	5.4	55
49	Electrical contacts in monolayer blue phosphorene devices. Nano Research, 2018, 11, 1834-1849.	5.8	55
50	First-principle calculation and assignment for vibrational spectra of Ba(Mg1/3Nb2/3)O3 microwave dielectric ceramic. Journal of Applied Physics, 2014, 115, .	1.1	54
51	Gate-tunable interfacial properties of in-plane ML MX₂ 1Tâ€²â€“2H heterojunctions. Journal of Materials Chemistry C, 2018, 6, 5651-5661.	2.7	54
52	Spontaneous valley splitting and valley pseudospin field effect transistors of monolayer VAgP₂Se₆. Nanoscale, 2018, 10, 13986-13993.	2.8	50
53	Assignment of Raman-active vibrational modes of MgTiO3. Journal of Applied Physics, 2008, 104, .	1.1	49
54	Holey graphite: A promising anode material with ultrahigh storage for lithium-ion battery. Electrochimica Acta, 2020, 346, 136244.	2.6	49

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55	High performance silicene nanoribbon field effect transistors with current saturation. European Physical Journal B, 2012, 85, 1.	0.6	48
56	High-performance sub-10-nm monolayer black phosphorene tunneling transistors. Nano Research, 2018, 11, 2658-2668.	5.8	47
57	Room-temperature giant magnetoresistance over one billion percent in a bare graphene nanoribbon device. Physical Review B, 2010, 81, .	1.1	44
58	Direct Observation of Semiconductorâ€“Metal Phase Transition in Bilayer Tungsten Diselenide Induced by Potassium Surface Functionalization. ACS Nano, 2018, 12, 2070-2077.	7.3	44
59	Reaction Mechanism and Structural Evolution of Fluorographite Cathodes in Solidâ€State K/Na/Li Batteries. Advanced Materials, 2021, 33, e2006118.	11.1	44
60	Origin of 3.45 eV Emission Line and Yellow Luminescence Band in GaN Nanowires: Surface Microwire and Defect. ACS Nano, 2015, 9, 9276-9283.	7.3	43
61	Electrically controlled electron transfer and resistance switching in reduced graphene oxide noncovalently functionalized with thionine. Journal of Materials Chemistry, 2012, 22, 16422.	6.7	42
62	Silicene nanomesh. Scientific Reports, 2015, 5, 9075.	1.6	42
63	Schottky Contact in Monolayer WS₂ Fieldâ€Effect Transistors. Advanced Theory and Simulations, 2019, 2, 1900001.	1.3	42
64	Does the Dirac cone of germanene exist on metal substrates?. Physical Chemistry Chemical Physics, 2016, 18, 19451-19456.	1.3	39
65	Performance Limit of Monolayer WSe₂ Transistors; Significantly Outperform Their MoS₂ Counterpart. ACS Applied Materials & Interfaces, 2020, 12, 20633-20644.	4.0	39
66	Sub-5-nm Monolayer Silicane Transistor: A First-Principles Quantum Transport Simulation. Physical Review Applied, 2020, 14, .	1.5	38
67	Electron transport through single endohedral Ce@C<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>82</mml:mn></mml:msub></mml:math>metallofullerenes. Physical Review B, 2012, 86, .	1.1	35
68	Two-dimensional single-layer PC6 as promising anode materials for Li-ion batteries: The first-principles calculations study. Applied Surface Science, 2020, 510, 145493.	3.1	35
69	n-Type Ohmic contact and p-type Schottky contact of monolayer InSe transistors. Physical Chemistry Chemical Physics, 2018, 20, 24641-24651.	1.3	33
70	Surface-Based Li⁺ Complex Enables Uniform Lithium Deposition for Stable Lithium Metal Anodes. ACS Applied Energy Materials, 2019, 2, 4602-4608.	2.5	32
71	A sub-10 nm monolayer ReS₂ transistor for low-power applications. Journal of Materials Chemistry C, 2019, 7, 1604-1611.	2.7	32
72	Monolayer GaS with high ion mobility and capacity as a promising anode battery material. Journal of Materials Chemistry A, 2019, 7, 14042-14050.	5.2	32

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73	Performance limit of monolayer MoSi₂N₄ transistors. Journal of Materials Chemistry C, 2021, 9, 14683-14698.	2.7	32
74	Can Carbon Nanotube Transistors Be Scaled Down to the Sub-5 nm Gate Length?. ACS Applied Materials & Interfaces, 2021, 13, 31957-31967.	4.0	32
75	Negative differential resistance in parallel single-walled carbon nanotube contacts. Physical Review B, 2011, 83, .	1.1	31
76	Sub-10 nm tunneling field-effect transistors based on monolayer group IV mono-chalcogenides. Nanoscale, 2019, 11, 23392-23401.	2.8	30
77	Monolayer Honeycomb Borophene: A Promising Anode Material with a Record Capacity for Lithium-Ion and Sodium-Ion Batteries. Journal of the Electrochemical Society, 2020, 167, 090527.	1.3	28
78	Is graphite nanomesh a promising anode for the Na/K-Ions batteries?. Carbon, 2021, 176, 242-252.	5.4	28
79	Dependence of excited-state properties of tellurium on dimensionality: From bulk to two dimensions to one dimensions. Physical Review B, 2018, 98, .	1.1	27
80	Reexamination of the Schottky Barrier Heights in Monolayer MoS₂ Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 4717-4726.	2.4	27
81	Sub-5 nm monolayer germanium selenide (GeSe) MOSFETs: towards a high performance and stable device. Nanoscale, 2020, 12, 15443-15452.	2.8	27
82	Separation of metallic singleâ€walled carbon nanotubes using various amines. Physica Status Solidi (B): Basic Research, 2010, 247, 2641-2644.	0.7	25
83	Anomalous Light Emission and Wide Photoluminescence Spectra in Graphene Quantum Dot: Quantum Confinement from Edge Microstructure. Journal of Physical Chemistry Letters, 2016, 7, 2888-2892.	2.1	25
84	Synergism of Rare Earth Trihydrides and Graphite in Lithium Storage: Evidence of Hydrogenâ€Enhanced Lithiation. Advanced Materials, 2018, 30, 1704353.	11.1	25
85	Imprinting Ferromagnetism and Superconductivity in Single Atomic Layers of Molecular Superlattices. Advanced Materials, 2020, 32, e1907645.	11.1	25
86	Structure and Electronic and Transport Properties of Transition Metal Intercalated Graphene and Graphene-Hexagonal-Boron-Nitride Bilayer. Journal of Physical Chemistry C, 2011, 115, 25273-25280.	1.5	23
87	Evidence of Type-II Band Alignment in III-nitride Semiconductors: Experimental and theoretical investigation for In0.17Al0.83N/GaN heterostructures. Scientific Reports, 2014, 4, 6521.	1.6	23
88	Giant tunnelling electroresistance through 2D sliding ferroelectric materials. Materials Horizons, 2022, 9, 1422-1430.	6.4	23
89	Structural and electronic properties of heterofullerene C59P. Molecular Physics, 2001, 99, 1203-1207.	0.8	22
90	Interfacial Properties of Monolayer Antimonene Devices. Physical Review Applied, 2019, 11, .	1.5	22

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91	Layer-Dependent Giant Magnetoresistance in Two-Dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Cr</mml:mi><mml:mi>PS</mml:mi></mml:mrow><mml:mn>4</mml:mn></m Magnetic Tunnel Junctions. Physical Review Applied, 2021, 16, .	1.5	22
92	Performance Limit of Ultrathin GaAs Transistors. ACS Applied Materials & Interfaces, 2022, 14, 23597-23609.	4.0	22
93	Evolution of the Electronic Properties of Metallic Single-Walled Carbon Nanotubes with the Degree of CCl2Covalent Functionalization. Journal of Physical Chemistry B, 2006, 110, 5655-5658.	1.2	21
94	Preparation of transparent and conductive thin films of metallic single-walled carbon nanotubes. Journal of Materials Chemistry, 2008, 18, 4189.	6.7	21
95	Sub-5 nm monolayer black phosphorene tunneling transistors. Nanotechnology, 2018, 29, 485202.	1.3	21
96	Device performance limits and negative capacitance of monolayer GeSe and GeTe tunneling field effect transistors. RSC Advances, 2020, 10, 16071-16078.	1.7	21
97	Unusual Fermiâ€Level Pinning and Ohmic Contact at Monolayer Bi 2 O 2 Seâ€“Metal Interface. Advanced Theory and Simulations, 2019, 2, 1800178.	1.3	20
98	Planar Directionâ€Dependent Interfacial Properties in Monolayer In₂Se₃â€“Metal Contacts. Physica Status Solidi (B): Basic Research, 2020, 257, 1900198.	0.7	19
99	Sub-5 nm Gate Length Monolayer MoTe₂ Transistors. Journal of Physical Chemistry C, 2021, 125, 19394-19404.	1.5	19
100	Interplay of single-wall carbon nanotubes and encapsulatedLa@C82,La2@C80, andSc3N@C80. Physical Review B, 2005, 71, .	1.1	18
101	First-Principles Calculation of ¹³C NMR Chemical Shifts of Infinite Single-Walled Carbon Nanotubes: New Data for Large-Diameter and Four-Helical Nanotubes. Journal of Physical Chemistry C, 2008, 112, 16417-16421.	1.5	18
102	First-principles study of hydrogen-passivated single-crystalline silicon nanotubes: electronic and optical properties. Nanotechnology, 2007, 18, 505707.	1.3	17
103	Static and Optical Transverse and Longitudinal Screened Polarizabilities of Boron Nitride Nanotubes. Journal of Physical Chemistry C, 2007, 111, 3285-3289.	1.5	17
104	A computational study of monolayer hexagonal WTe₂ to metal interfaces. Physica Status Solidi (B): Basic Research, 2017, 254, 1600837.	0.7	17
105	Pervasive Ohmic Contacts in Bilayer Bi₂O₂Seâ€“Metal Interfaces. Journal of Physical Chemistry C, 2019, 123, 8923-8931.	1.5	17
106	Far infrared reflection spectrum and IR-active modes of MgTiO3. Journal of Applied Physics, 2008, 103, 074105.	1.1	16
107	Tunable Valley Polarization and Valley Orbital Magnetic Moment Hall Effect in Honeycomb Systems with Broken Inversion Symmetry. Scientific Reports, 2015, 5, 13906.	1.6	16
108	Ohmic contact in graphene/SnSe2 Van Der Waals heterostructures and its device performance from ab initio simulation. Journal of Materials Science, 2020, 55, 4321-4331.	1.7	16

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109	Highâ€Performance Spin Filters and Spin Field Effect Transistors Based on Bilayer VSe₂. Advanced Theory and Simulations, 2021, 4, 2000238.	1.3	16
110	INTERACTION OF SINGLE-WALLED CARBON NANOTUBES WITH AMINE. Nano, 2012, 07, 1130001.	0.5	15
111	Interfacial Properties of Monolayer SnSâ€“Metal Contacts. Journal of Physical Chemistry C, 2018, 122, 12322-12331.	1.5	15
112	Can ultra-thin Si FinFETs work well in the sub-10 nm gate-length region?. Nanoscale, 2021, 13, 5536-5544.	2.8	15
113	Electron localization and emission mechanism in wurtzite (Al, In, Ga)N alloys. Physica Status Solidi (B): Basic Research, 2010, 247, 109-114.	0.7	14
114	Improvement of alkali metal ion batteries <i>via</i> interlayer engineering of anodes: from graphite to graphene. Nanoscale, 2021, 13, 12521-12533.	2.8	14
115	Bilayer Tellurene: A Potential pâ€Type Channel Material for Subâ€10 nm Transistors. Advanced Theory and Simulations, 2021, 4, 2000252.	1.3	14
116	Selection of single-walled carbon nanotubes according to both their diameter and chirality via nanotweezers. Nano Research, 2010, 3, 296-306.	5.8	13
117	n- and p-type ohmic contacts at monolayer gallium nitrideâ€“metal interfaces. Physical Chemistry Chemical Physics, 2018, 20, 24239-24249.	1.3	13
118	Computational Study of Ohmic Contact at Bilayer InSe-Metal Interfaces: Implications for Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 6898-6908.	2.4	13
119	Van der waals BP/InSe heterojunction for tunneling field-effect transistors. Journal of Materials Science, 2021, 56, 8563-8574.	1.7	13
120	Two-dimensional materials as a stabilized interphase for the solid-state electrolyte Li₁₀GeP₂S₁₂ in lithium metal batteries. Journal of Materials Chemistry A, 2021, 9, 4810-4821.	5.2	12
121	Layer-Dependent Photoabsorption and Photovoltaic Effects in Two-Dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mrow><mml:mrow><m mathvariant="normal">O</mml:mi></mml:mrow></mml:mrow><mml:mn>2</mml:mn></mml:msub><mml:mi>X</mml:mi></mml:ma		

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127	Scaling Behavior of Magnetoresistance with the Layer Number in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Cr</mml:mi><mml:mi mathvariant="normal">I</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:math> Magnetic Tunnel Junctions. Physical Review Applied, 2022, 17, .	1.5	10
128	Directly imaging the structureâ€“property correlation of perovskites in crystalline microwires. Journal of Materials Chemistry A, 2019, 7, 13305-13314.	5.2	9
129	Direct Observation of Li Migration into V₅S₈: Order to Antisite Disorder Intercalation Followed by the Topotactic-Based Conversion Reaction. ACS Applied Materials & Interfaces, 2020, 12, 36320-36328.	4.0	9
130	Ohmic contacts of monolayer Tl2O field-effect transistors. Journal of Materials Science, 2020, 55, 11439-11450.	1.7	9
131	First-principles simulation of monolayer hydrogen passivated Bi₂O₂S₂â€“metal interfaces. Physical Chemistry Chemical Physics, 2020, 22, 7853-7863.	1.3	9
132	Device performance limit of monolayer SnSe2 MOSFET. Nano Research, 0, , 1.	5.8	9
133	Oligonucleotide Discrimination Enabled by Tannic Acid-Coordinated Film-Coated Solid-State Nanopores. Langmuir, 2022, 38, 6443-6453.	1.6	9
134	Structural and electronic properties of endohedral phosphorus fullerene P@C60: an off-centre displacement of P inside the cage. Molecular Physics, 2001, 99, 1199-1202.	0.8	7
135	EXTRACTION OF METALLIC NANOTUBES OF ZEOLITE-SUPPORTED SINGLE-WALLED CARBON NANOTUBES SYNTHESIZED FROM ALCOHOL. Nano, 2007, 02, 221-226.	0.5	7
136	Enhanced manyâ€body effects in oneâ€dimensional linear atomic chains. Physica Status Solidi (B): Basic Research, 2013, 250, 1636-1643.	0.7	7
137	Laser ablation of pristine Fe foil for constructing a layer-by-layer SiO₂/Fe₂O₃/Fe integrated anode for high cycling-stability lithium-ion batteries. Physical Chemistry Chemical Physics, 2021, 23, 10365-10376.	1.3	7
138	EFFECTS OF ORIENTATION ON THE ELECTRONIC STRUCTURE OF K3C60. Modern Physics Letters B, 1996, 10, 1417-1422.	1.0	6
139	Adsorption configurations of carbon monoxide on gold monolayer supported by graphene or monolayer hexagonal boron nitride: a first-principles study. European Physical Journal B, 2013, 86, 1.	0.6	6
140	Origin of the wide band gap from 0.6 to 2.3 eV in photovoltaic material InN: quantum confinement from surface nanostructure. Journal of Materials Chemistry A, 2016, 4, 17412-17418.	5.2	6
141	Layerâ€Controlled Lowâ€Power Tunneling Transistors Based on SnS Homojunction. Advanced Theory and Simulations, 2021, 4, 2000290.	1.3	6
142	Tuning graphene nanoribbon field effect transistors via controlling doping level. Theoretical Chemistry Accounts, 2011, 130, 483-489.	0.5	5
143	Electronic structures and properties of lanthanide hexaboride nanowires. Journal of Applied Physics, 2013, 114, 143709.	1.1	5
144	Correlating the electronic structures of metallic/semiconducting MoTe2 interface to its atomic structures. National Science Review, 2021, 8, nwaa087.	4.6	5

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145	Phase transition and topological transistors based on monolayer Na₃Bi nanoribbons. Nanoscale, 2021, 13, 15048-15057.	2.8	5
146	STRUCTURAL AND ELECTRONIC PROPERTIES OF ONE DIMENSIONAL KxC60 CRYSTAL ENCAPSULATED IN CARBON NANOTUBE. International Journal of Modern Physics B, 2007, 21, 1705-1714.	1.0	4
147	Anomalous heavy doping in chemical-vapor-deposited titanium trisulfide nanostructures. Physical Review Materials, 2021, 5, .	0.9	3
148	Device simulation of GeSe homojunction and vdW GeSe/GeTe heterojunction TFETs for high-performance application. Journal of Computational Electronics, 2022, 21, 401-410.	1.3	3
149	TWO-COMPONENT SUPERCONDUCTIVITY FOR DOPED FULLERENES. Modern Physics Letters B, 1996, 10, 823-829.	1.0	2
150	Application of the Recursion Method to the Electronic Structures of Simple-Cubic Na2CsC60 and Body-Centered-Cubic K6C60. Modern Physics Letters B, 1997, 11, 659-665.	1.0	2
151	Graphene Acoustic Phononâ€Mediated Pseudoâ€Landau Levels Tailoring Probed by Scanning Tunneling Spectroscopy. Small, 2020, 16, 1905202.	5.2	2
152	NUMERICAL APPLICATION OF THE RECURSION METHOD TO THE ELECTRONIC STRUCTURE OF C60. Modern Physics Letters B, 1996, 10, 1133-1139.	1.0	1
153	Tunable and sizable band gap in silicene by surface adsorption. , 0, .		1